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PATENT Atty. Dkt. AMAT/7729/TCG/EPI/RKK

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Singh, et al.

Serial No.: 10/688,797

Confirmation No.: 9712

Filed:

JUN 1 7 2005

October 17, 2003

For:

Silicon-Containing Layer

Deposition with Silicon

Compounds

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Group Art Unit: 1762

Examiner:

Unknown

MAIL STOP AMENDMENT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

CERTIFICATE OF MAILING 37 CFR 1.8

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The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Supplemental Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Supplemental Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

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If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/7729/KMT.

Respectfully submitted,

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Substitute for form 1449A/PTO				Application Number	10/688,426	OIPA	
				Filing Date	October 17, 200	03/	$\overline{\lambda}$
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	APPLICANT			Examiner Name	Unknown	To an artis	<i></i>
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	Substitute	for form 1449A/PTO			Application Number	10/688,426	
					Filing Date	October 17, 2003	
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	DISCLOSURE STATEMENT BY APPLICANT				Group Art Unit	1762	
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		(Use as many sheets as ne	cessary)	Attorney Docket Number	AMAT/7729/TCG/EPI/RKK	
	Sheet	2	of	2	Submission Date	June 17 . 2005	

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Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²
C3	Sedgwick, et al. "Selective SiGe and heavily As doped Si deposited at low temperature by atmospheric pressure chemical vapor deposition", Journal of Vacuum Science and Technology: Part B, American Institute of Physics. New York, US, vol. 11, no. 3, 1 May 1993, pp. 1124-1128	7
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	No. ¹	Cite No.1 Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published Sedgwick, et al. "Selective SiGe and heavily As doped Si deposited at low temperature by atmospheric pressure chemical vapor deposition", Journal of Vacuum Science and Technology: Part B, American Institute of Physics. New York, US, vol. 11, no. 3, 1 May 1993, pp. 1124-1128 Uchino, et al. "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1 µm CMOS ULSIs", Electron Devices Meeting, 1997. Technical Digest, International Washington, DC, USA 7-10 Dec. 1991.

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